

APPLICATIONS

Unit

$V_{CE}=1700V, V_{GE}=0V, T_J=150$

20

mA

mA

nA

μC

nF

nF

ns

ns

ns

ns

ns

ns

ns

Unit
K
K

Unit

V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.), t=1minute		V
Torque	to heatsink	Recommended M5	2.5~5	Nm
	to terminal	Recommended M6	3~5	Nm
Weight			350	g

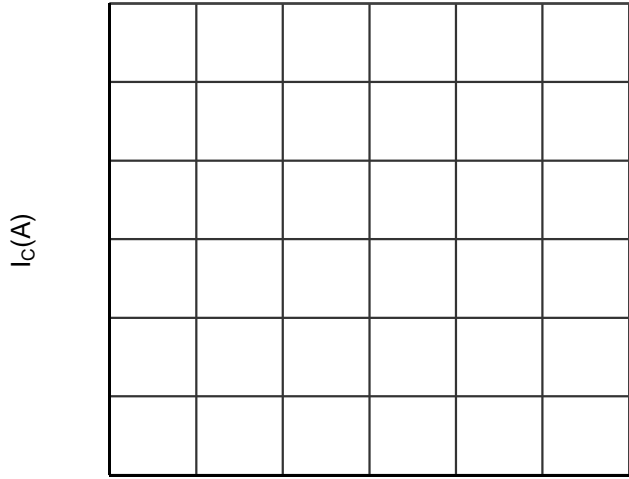


Figure 3. Typical Transfer characteristics IGBT-inverter

$E_{on}E_{off}(mJ)$

$R_g \Omega$

Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

mJ

)

MMG600WB170B6E4N

$I_F(A)$

$E_{REC}(mJ)$

$V_F(V)$

Figure 9. Diode Forward Characteristics Diode -inverter

$R_g \text{ } \mu s$

Figure 10. Switching Energy vs Gate Resistor Diode -inverter

n

Figure 14. Circuit Diagram